

FIG.1

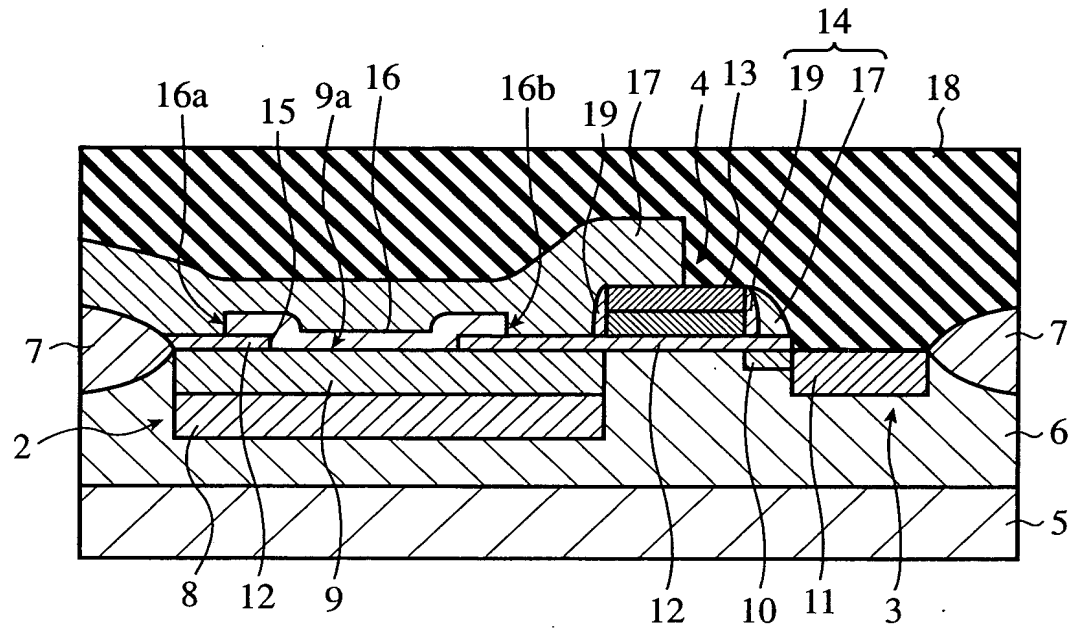


FIG.4

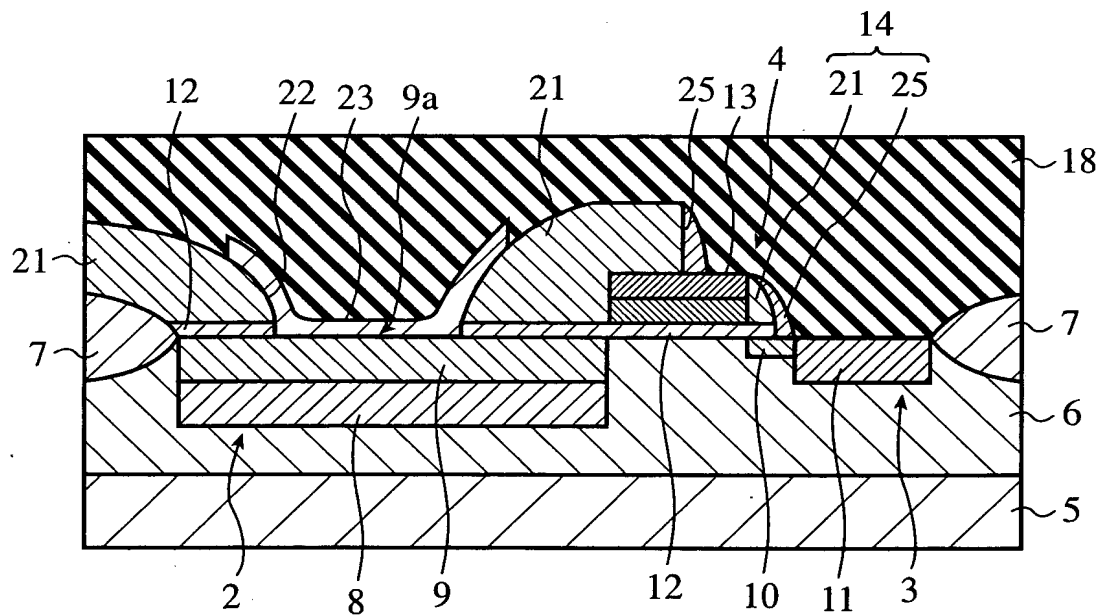


FIG.2A

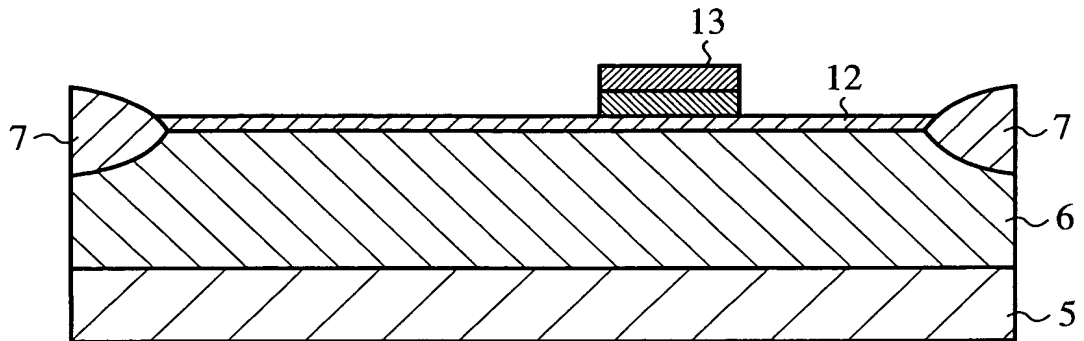


FIG.2B

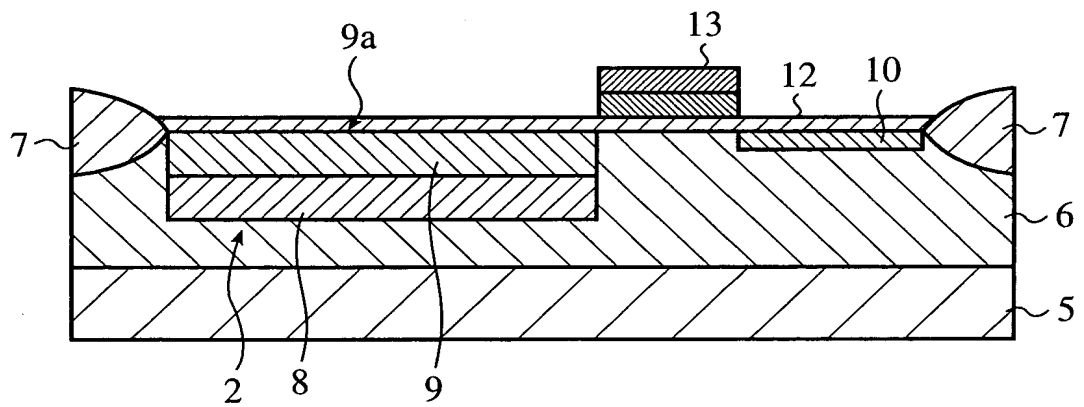
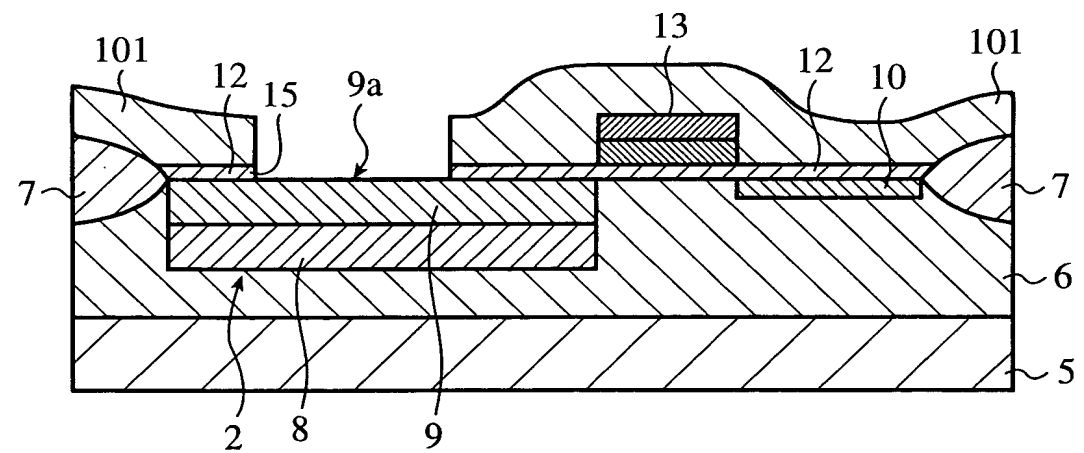


FIG.2C



A cross-sectional view of a semiconductor device. The device consists of a substrate with multiple layers. A central structure is formed on the substrate, featuring a series of rectangular blocks (15, 16, 9a, 102, 16b) stacked vertically. A layer (13) is positioned to the right of the central structure. A layer (19) is located below the central structure. A layer (12) is located below the layer (13). A layer (10) is located below the layer (12). The substrate is labeled with 7, 6, and 5. Other labels include 16a, 15, 16, 9a, 102, 16b, 19, 13, 12, 10, 12, 2, 8, and 9.

This cross-sectional view shows a substrate with layers 5, 6, and 7. A central structure 2 is embedded in layer 6, with layers 8 and 9 on its top surface. A top layer 103 is on the left, with a recessed area 17 containing a structure 12. To the right, a structure 13 is shown with a top layer 14 and a recessed area 17. Other labels include 7, 12, 16a, 16b, 19, and 10.



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FIG.6A

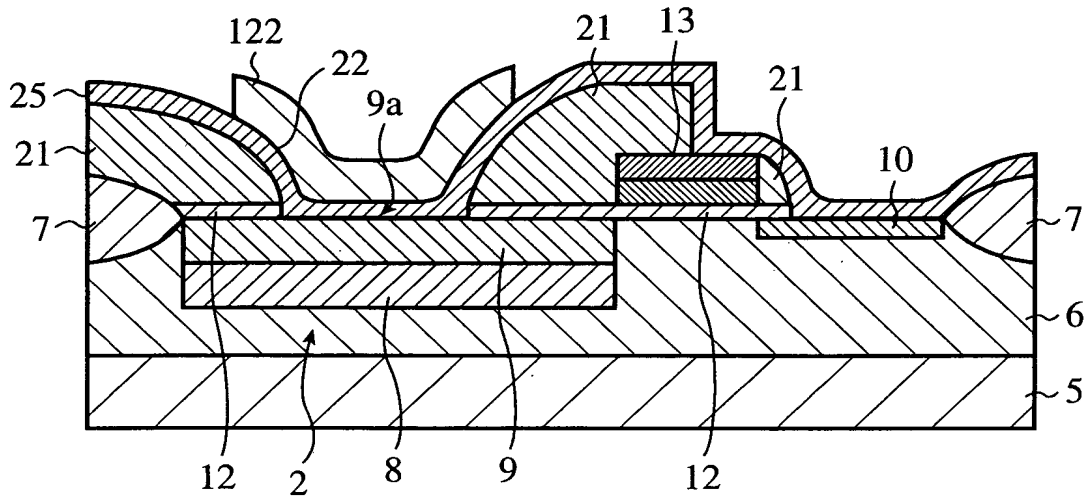
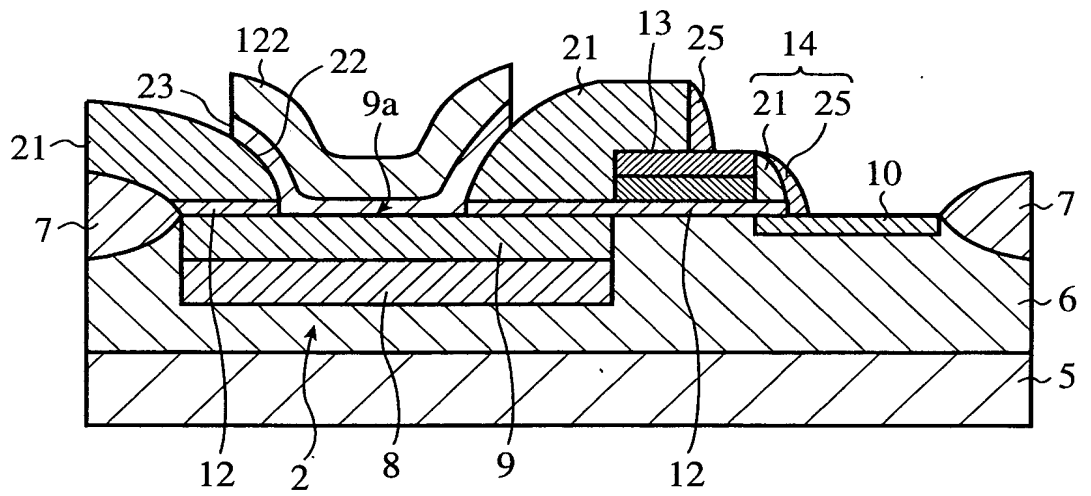


FIG.6B





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FIG.8A

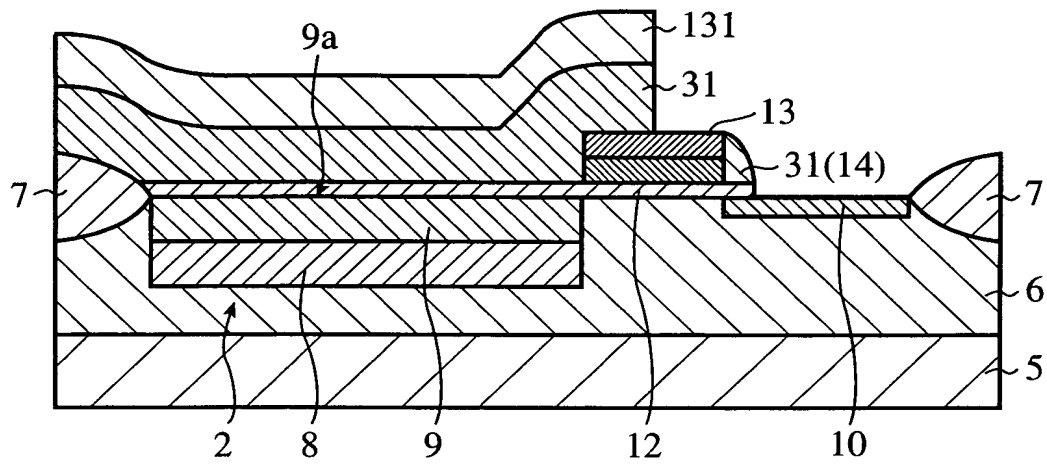


FIG.8B

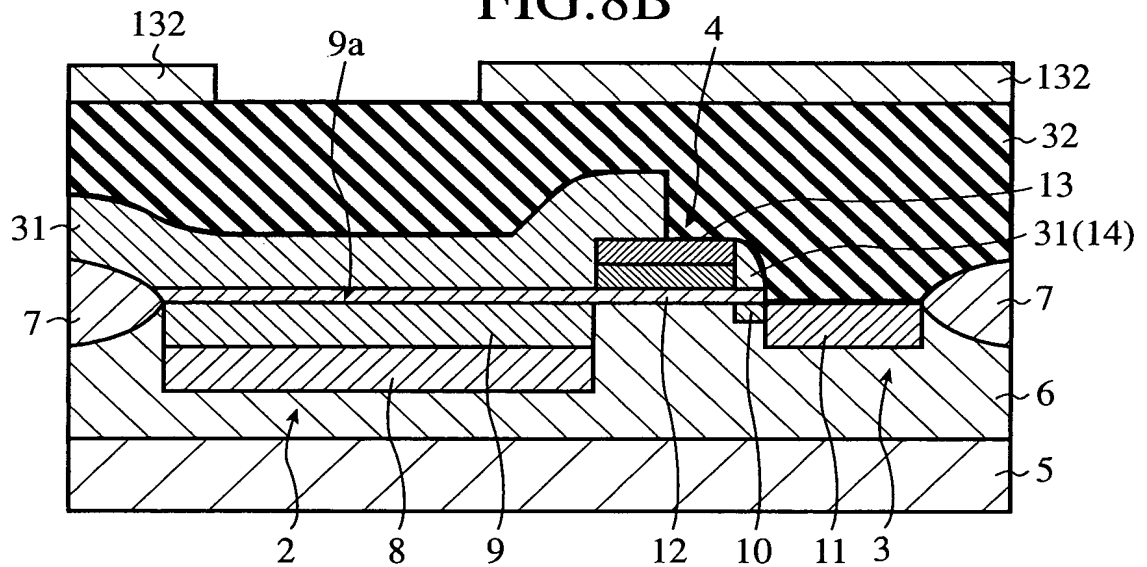
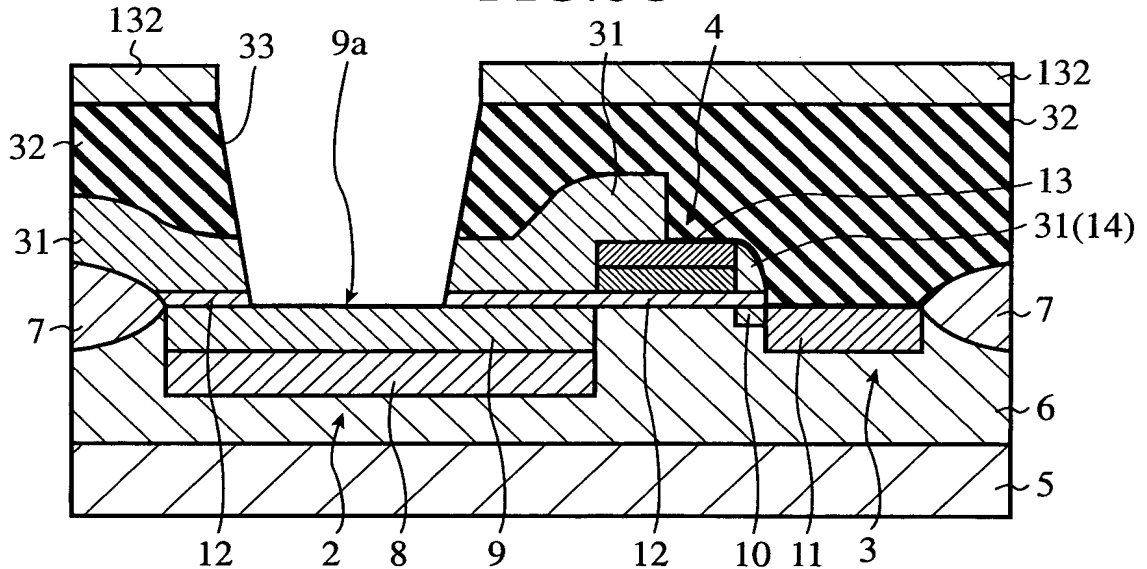


FIG.8C



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FIG.9A

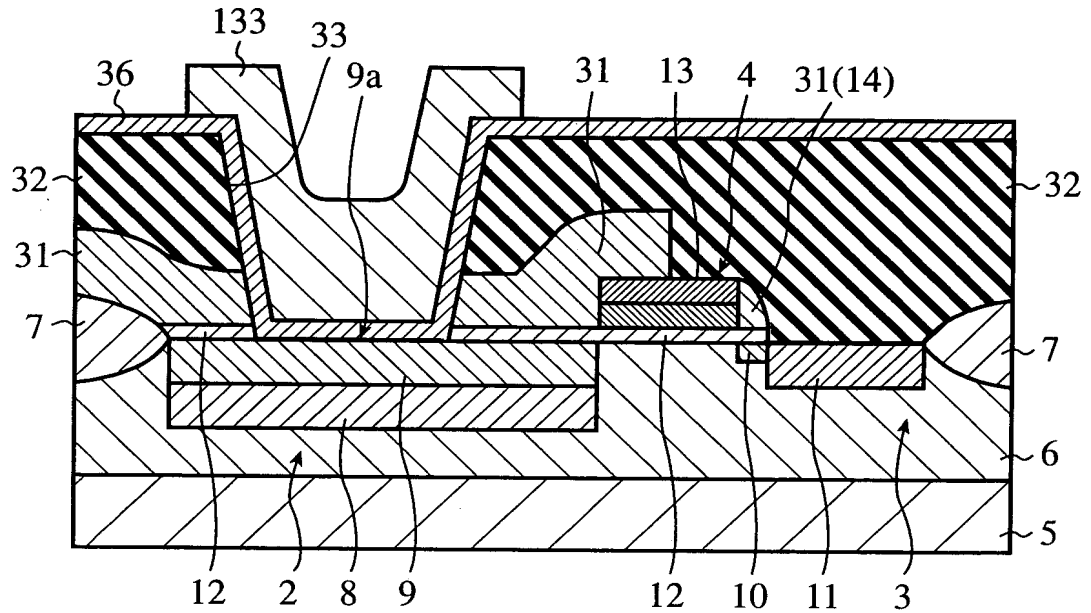
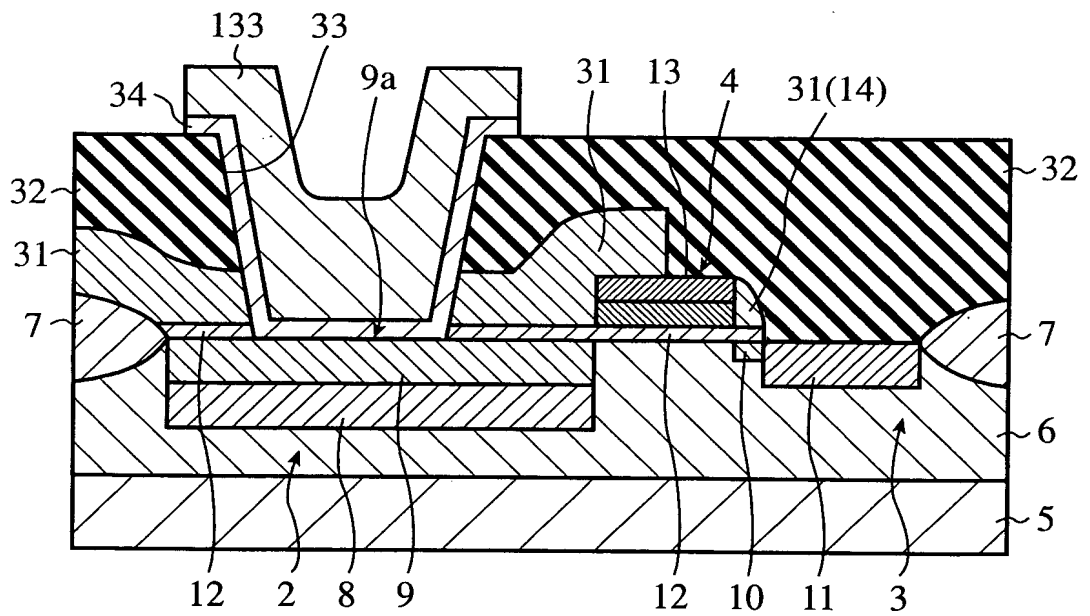


FIG.9B





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FIG.11A

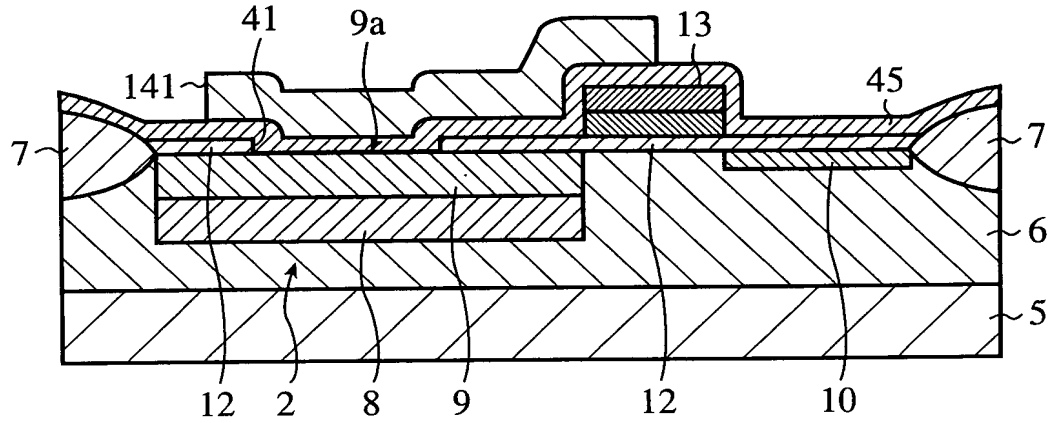


FIG.11B

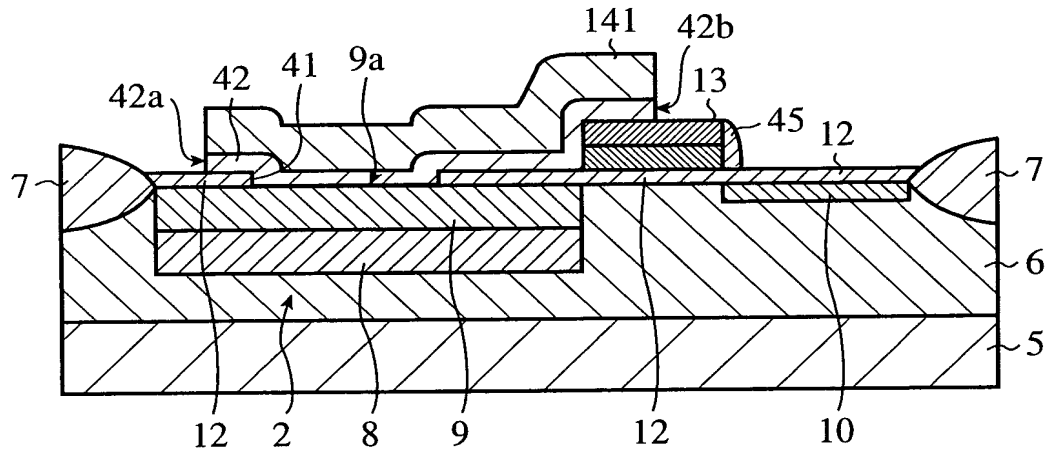


FIG.11C

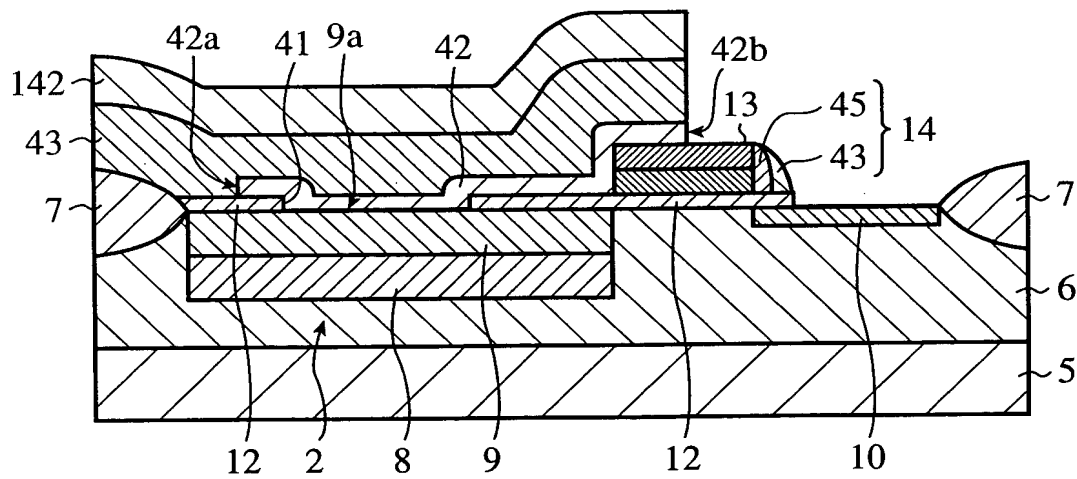


FIG.12

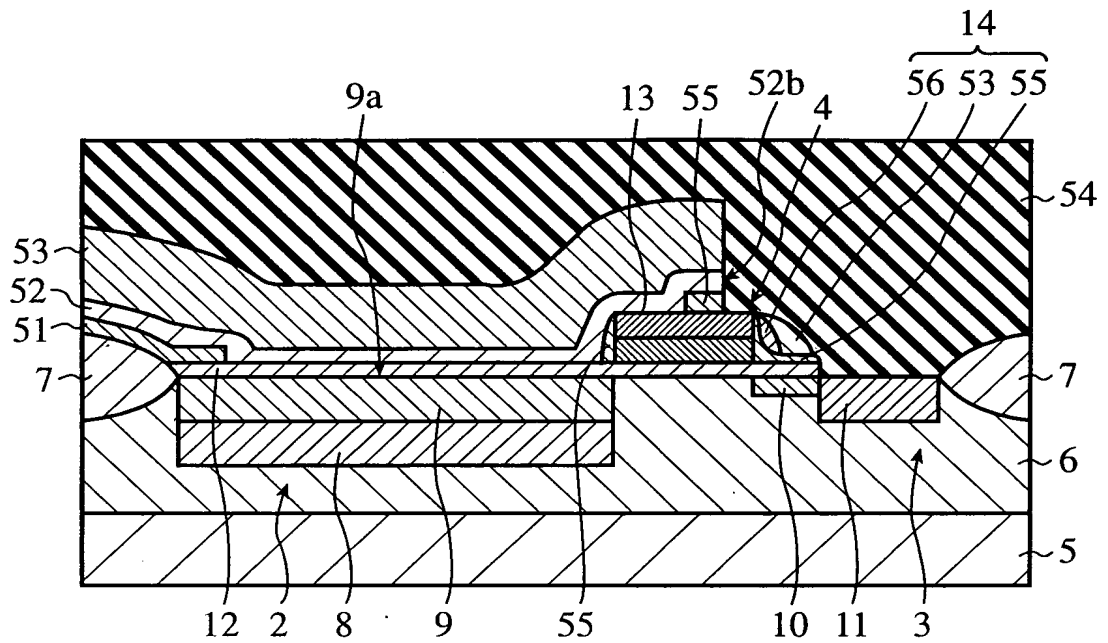
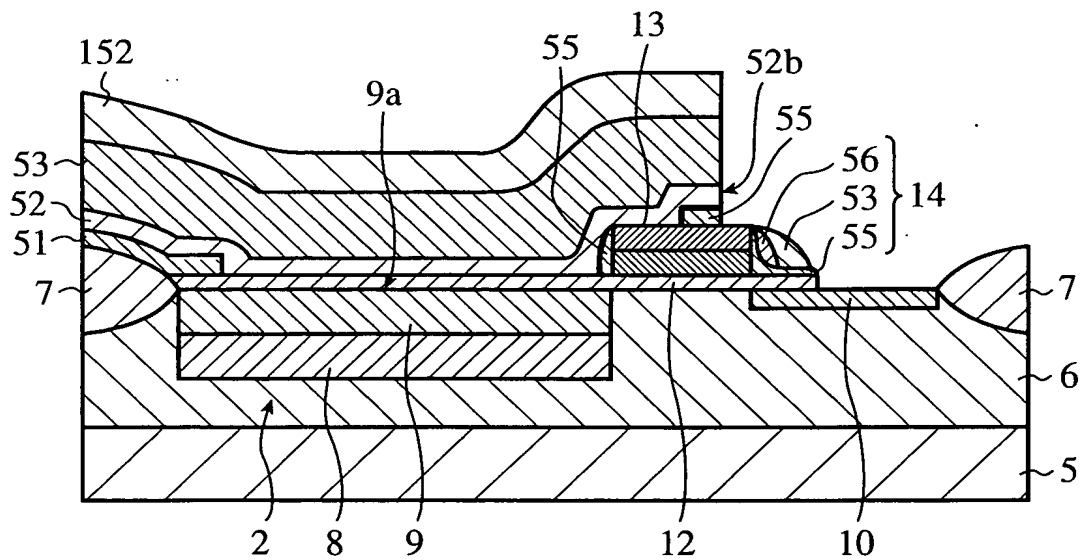


FIG.14



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FIG.13A

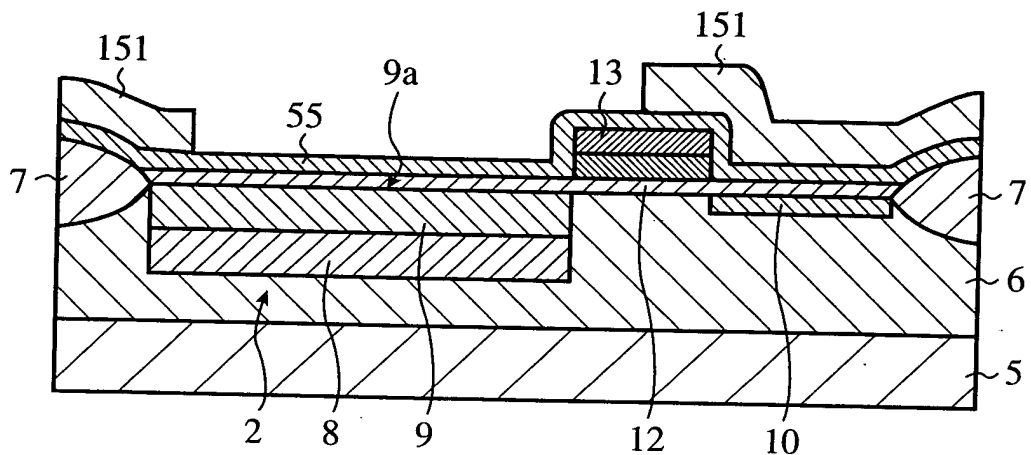


FIG.13B

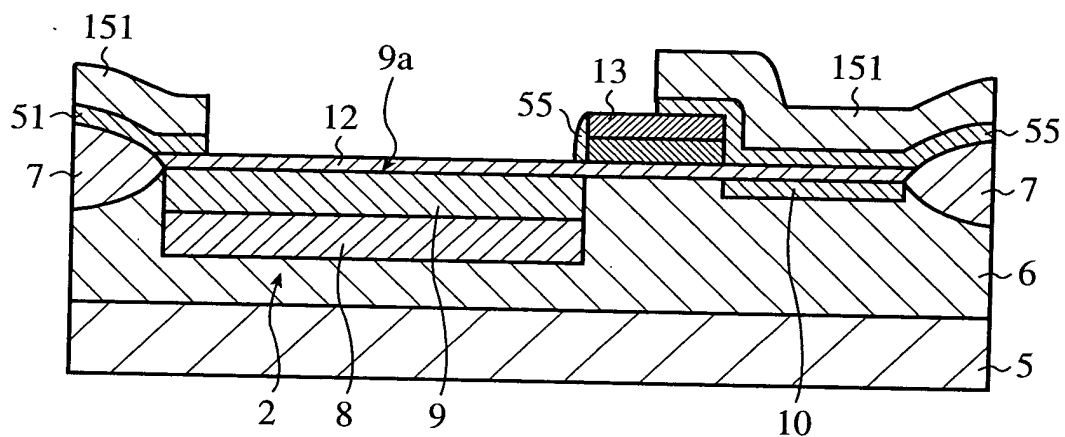


FIG.13C

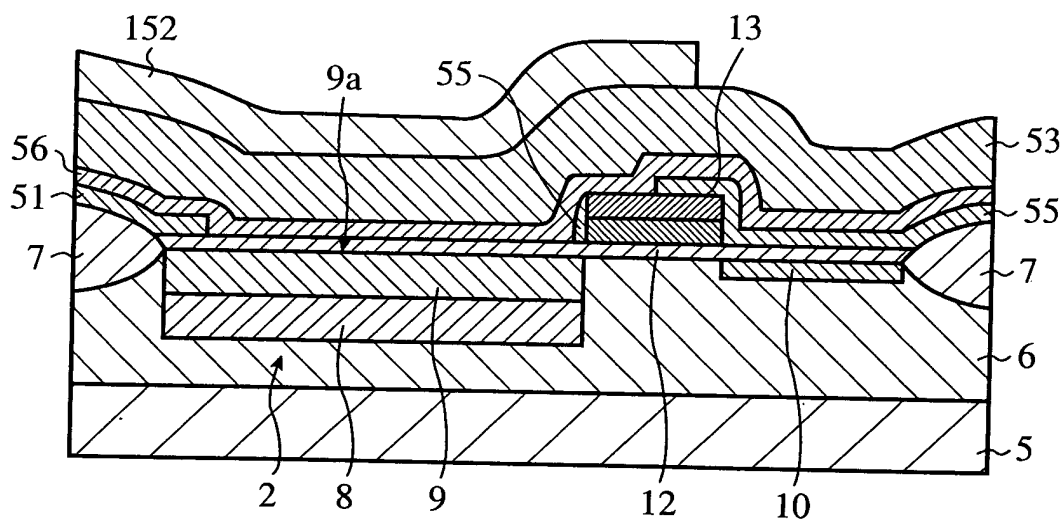




FIG.16A

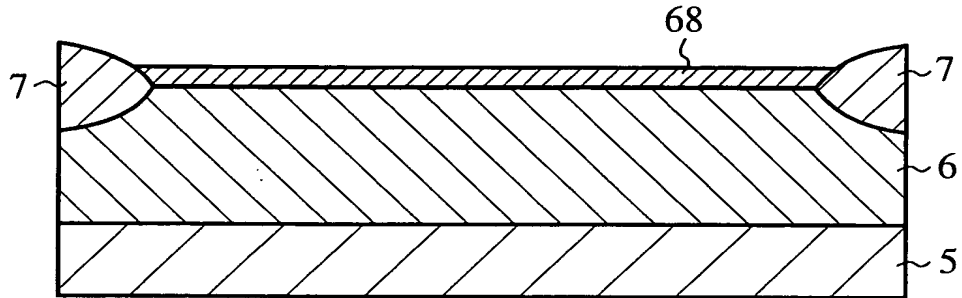


FIG.16B

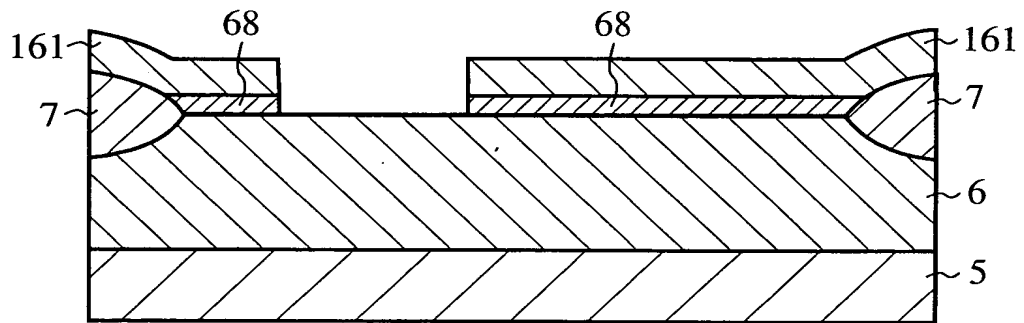


FIG.16C

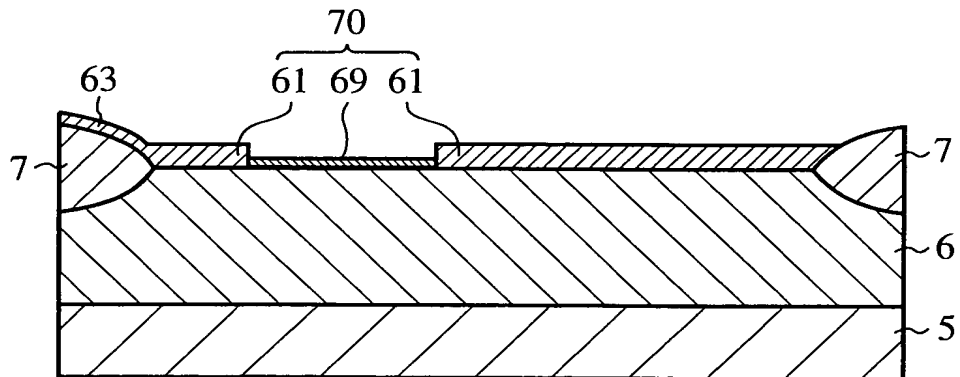


FIG.17A

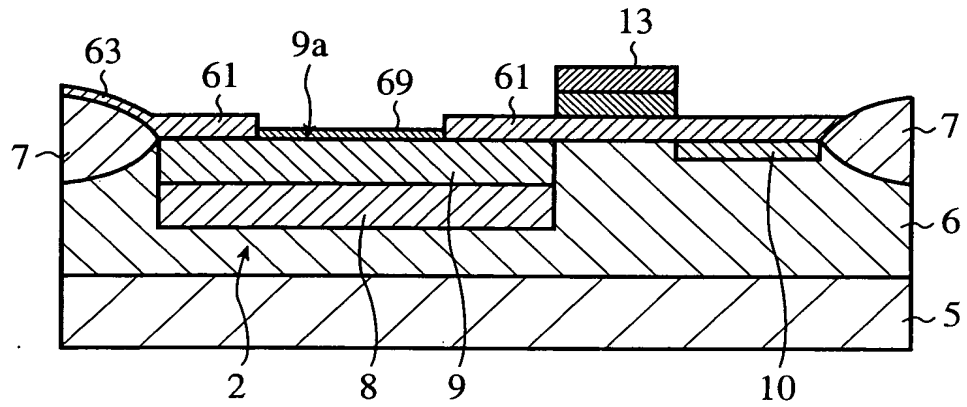


FIG.17B

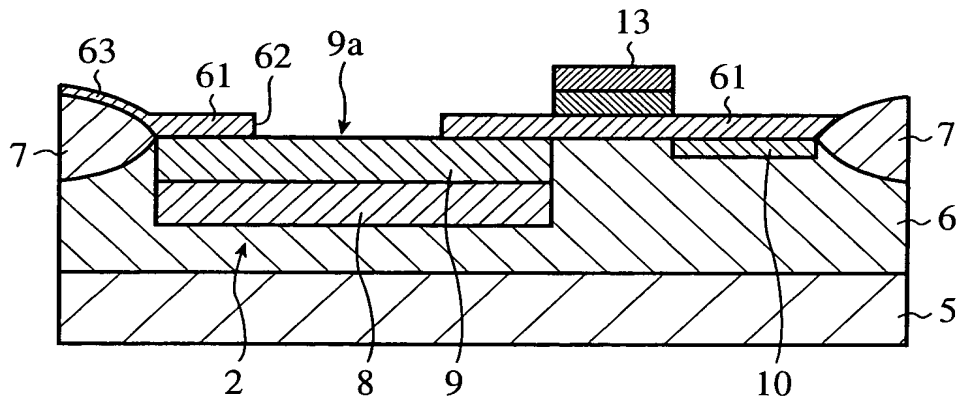


FIG.17C

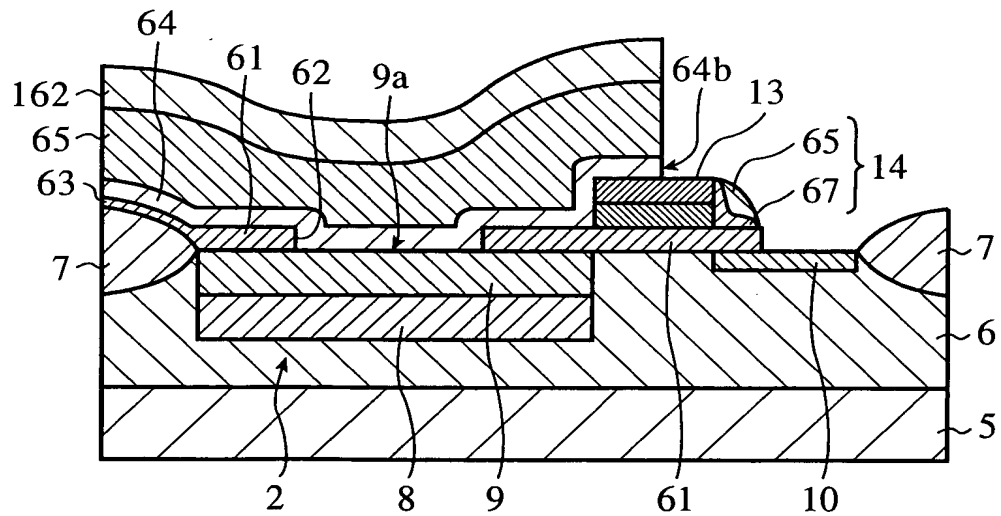


FIG.19A

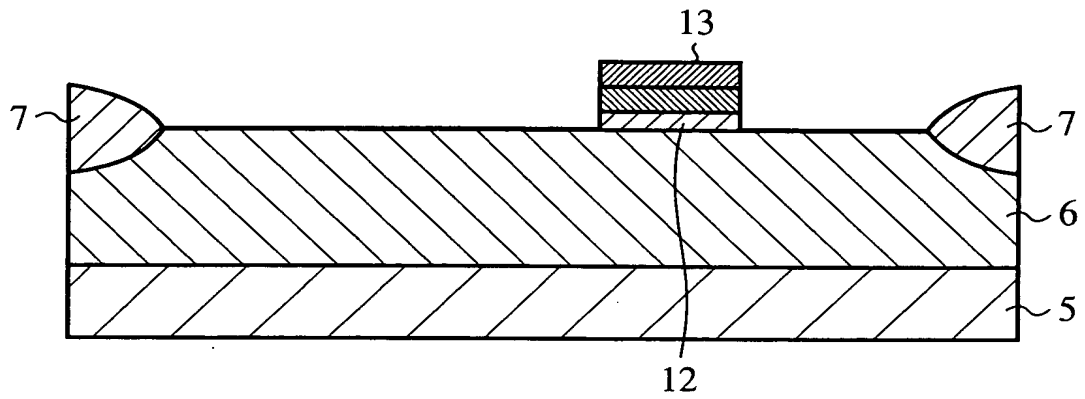


FIG.19B

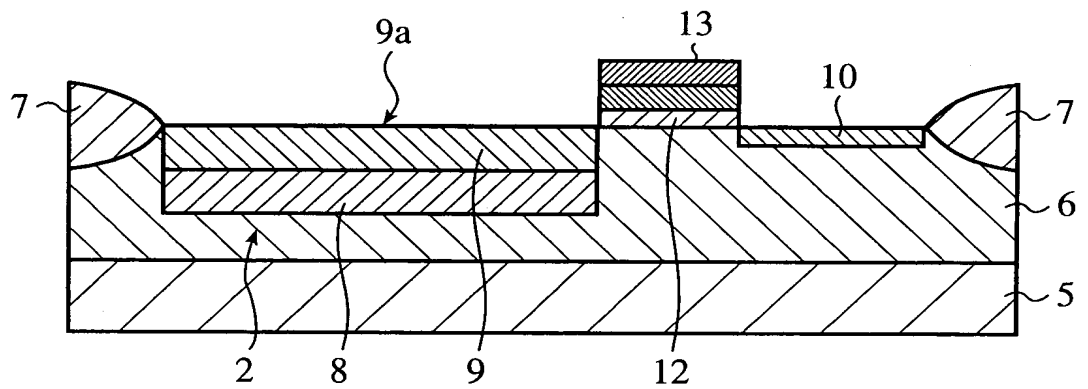


FIG.19C

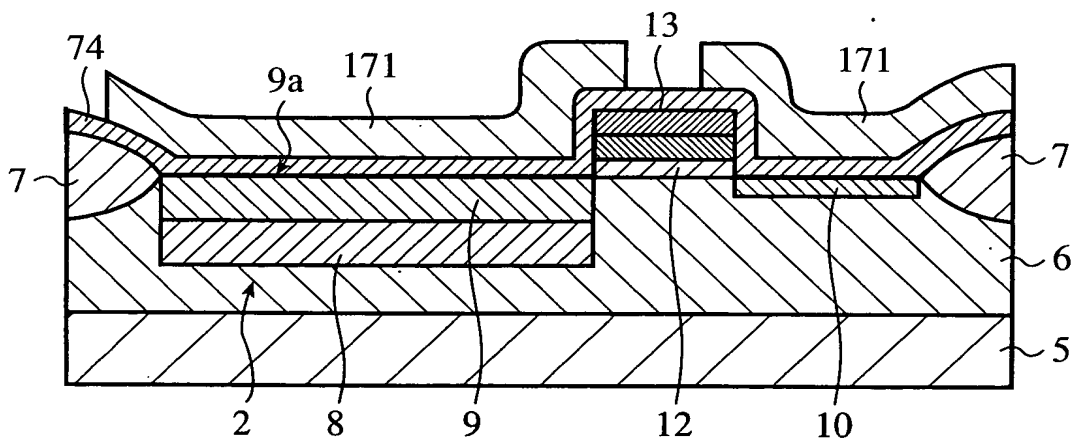


FIG.20A

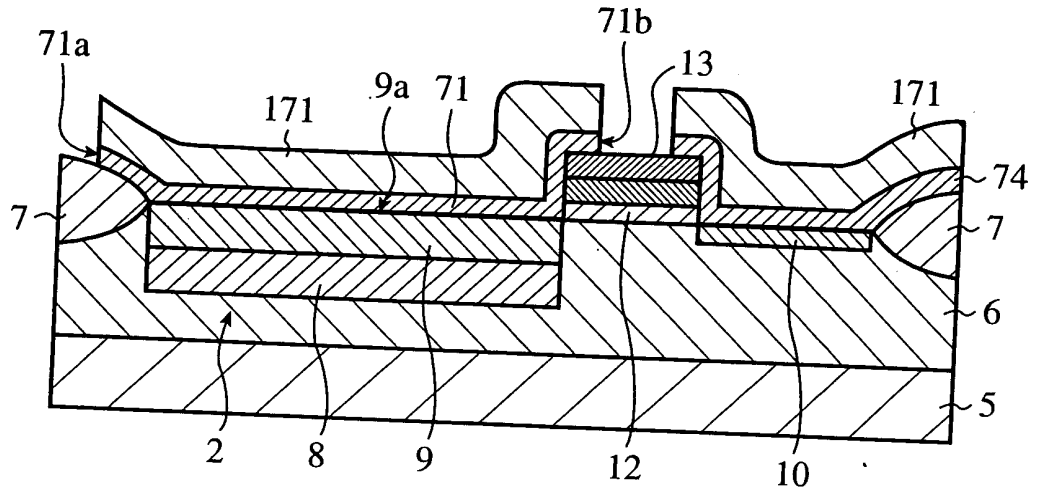


FIG.20B

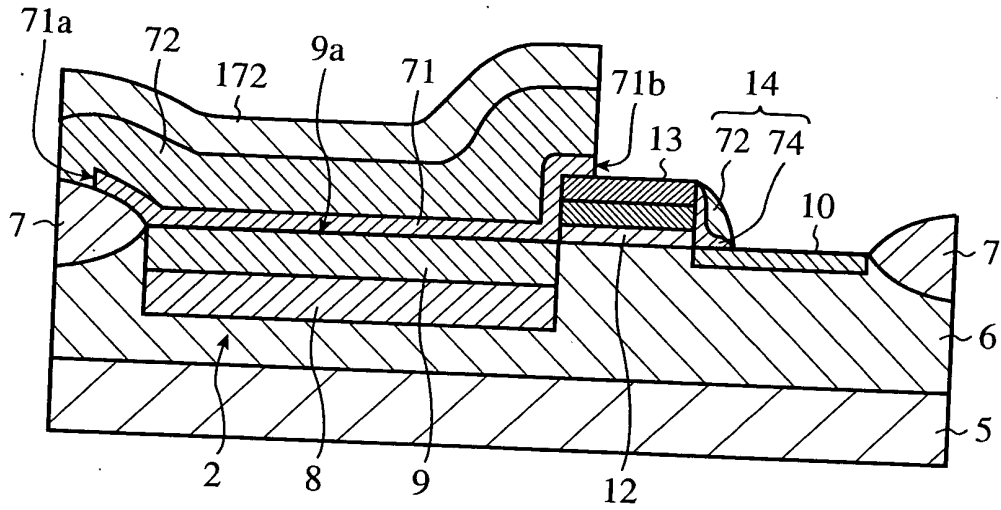




FIG.21

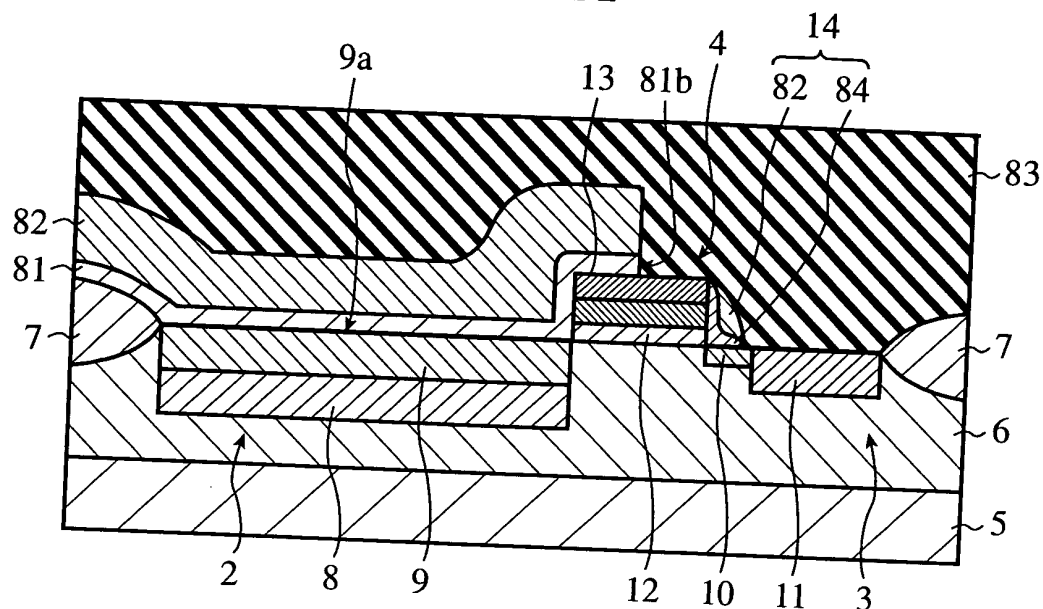


FIG.22A

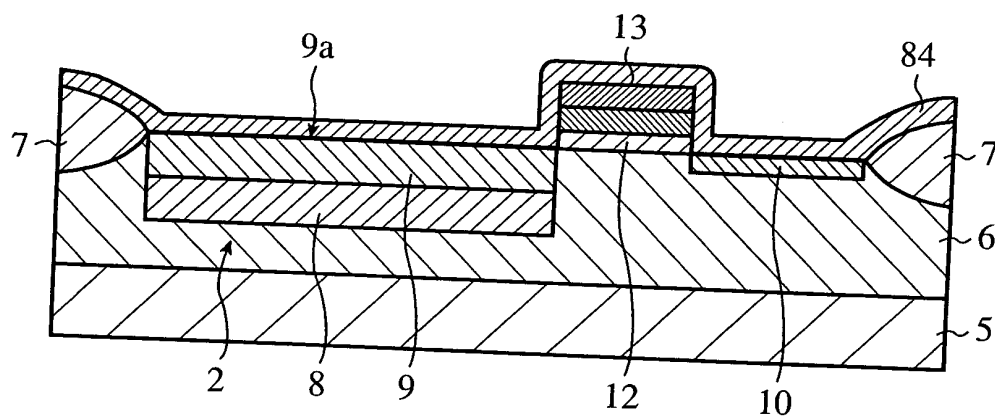


FIG. 22B

